In the Claims

CLAIMS

Claims 1-68 (Canceled).

69. (Currently amended) A semiconductor construction comprising:

a semiconductor substrate having a trench extending partially therein and upper surfaces formed adjacent the trench;

an oxide layer formed over the upper surfaces of the semiconductor substrate and having an uppermost surface; ~~and~~

an insulative material at least partially filling the trench and having a portion extending outward of the trench and the semiconductor substrate, the portion comprising an outermost upper surface formed elevationally above the uppermost surface of the oxide layer, the portion further comprising sidewalls connecting the outermost upper surface with the oxide layer, the sidewalls comprising first and second curved segments, the first curved segment extending from the outermost upper surface and comprising a first apex directed away from the semiconductor substrate, and the second curved segment extending from the first curved segment to the oxide layer and comprising a second apex directed toward the semiconductor substrate, the second apex being elevationally at or above the uppermost surface of the oxide layer, an entirety of the insulative material comprising the same stoichiometry, and wherein the outermost upper surface of the portion comprises a substantially planar surface; and

a polysilicon layer formed against the uppermost surface of the oxide layer and against the portion of the insulative material.

70. (Previously presented) The semiconductor construction of claim 69 wherein the insulative material comprises oxide.

Claims 71-72 (Canceled).

73. (Previously presented) The semiconductor construction of claim 69 wherein the trench comprises sidewalls connected by a bottom wall, and wherein the first curved segments of the portion are elevationally above and between the sidewalls of the trench.

74. (Previously presented) The semiconductor construction of claim 69 wherein the trench comprises sidewalls connected by a bottom wall, and wherein the first curved segments of the portion are directly over the bottom wall of the trench.

75. (Previously presented) The semiconductor construction of claim 69 wherein the trench comprises sidewalls intersecting the upper surfaces of the semiconductor substrate, the intersection being positioned elevationally directly below the second curved segment of the portion of the insulative material.

76. (Previously presented) The semiconductor construction of claim 69 wherein the trench comprises sidewalls extending substantially perpendicular relative the upper surfaces of the semiconductor substrate.

77. (Currently amended) The semiconductor construction of claim 69 wherein the trench comprises sidewalls connected by a bottom wall, and wherein the sidewalls <u>are</u> ~~form~~ <u>formed substantially at</u> right angles with the bottom wall.

78. (Previously presented) The semiconductor construction of claim 69 wherein the polysilicon layer directly contacts the sidewalls of the portion of the insulative material.

79. (Previously presented) The semiconductor construction of claim 69 wherein the polysilicon layer directly contacts the sidewalls and the outermost upper surface of the portion of the insulative material.

80. (New) The semiconductor construction of claim 69 wherein the upper surfaces of the semiconductor substrate are substantially planar surfaces, and wherein the upper surfaces are substantially parallel with the outermost upper surface of the portion of the insulative material.

81. (New) The semiconductor construction of claim 69 wherein the uppermost surface of the oxide layer is substantially planar, and wherein the uppermost surface is substantially parallel with the outermost upper surface of the portion of the insulative material.